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Renesas Technology Corp. Customer Support Dept. April 1, 2003



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The HD74LS373, 8-bit register features totem-pole three-state outputs designed specifically for driving highly-capacitive or relatively low-impedance loads. The high-impedance third state and increased high-logic-level drive provide this register with the capacity of being connected directly to and driving the bus lines in a bus-organized system without need for interface or pull-up components. They are particularly attractive for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

The eight latches are transparent D-type latches meaning that while the enable (G) is high the Q outputs will follow the data (D) inputs. When the enable is taken low the output will be latched at the level of the data that was setup.

EFUNCTION TABLE

	Output				
Output control	Enable G	D	Q		
L	н	Н	н		
L	Н	L.	L		
L	L	L ×			
Н	×	×	Z		

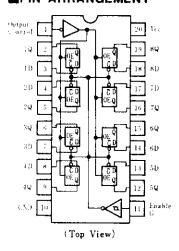
Notes: H = high level, L = low level,

X = irrelevant

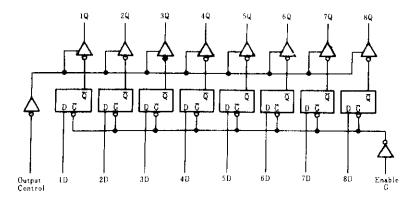
Q₀ = level of Q before the indicated steady-state input conditions were established.

Z = off (high-impedance) state of a three-state output

MPIN ARRANGEMENT



■BLOCK DIAGRAM



MRECOMMENDED OPERATING CONDITIONS

Item		Symbol	min	typ	max	Unit
Supply voltage		V_{cc}	4.75	5.00	5.25	V
Output voltage		V_{OH}			5.5	V
Output current		1 он	_	_	-2.6	mА
		Ior			24	mA
Enable pulse	"H" level		15			
width	"L" level	l w	15	_		ns
Data setup time		t su	5↓	-		ns
Data hold time		t s	25 ↓	_	_	ns

Note) 4: The arrow indicates the falling edge of clock pulse.

ELECTRICAL CHARACTERISTICS $(Ta=-20\sim+75^{\circ}C)$

Item	Symbol	Test Conditions		min	typ*	max	Unit
	VIH			2.0	_		V
Input voltage		Data inputs				0.7	V
	V _{IL}	G, Output control inputs		_	0.8	V	
	Von	$V_{CC} = 4.75 \text{V}, \ V_{IH} = 2 \text{V}, \ V_{IL} = V_{I}$	L mex, I _{OH} = -2.6mA	2.4			V
Output voltage		$V_{cc}-4.75V$, $V_{IB}-2V$,	Io1-12mA	_		0.4	V
	Vol	VIL - VIL max	IoL - 24mA			0.5	
	Іогн		Vo-2.7V			20	μΑ
Off-state output current	Iozi	$V_{\rm cc} = 5.25 \text{V}, V_{tH} = 2 \text{V}$	Vo-0.4V	_		-20	
	In	$V_{cc} = 5.25 \text{V}, V_l = 2.7 \text{V}$				20	μA
Input current	In.	V_{cc} = 5.25V, V_{t} = 0.4V			0.4	mA	
	I,	Vcc-5.25V, V1-7V	_		0.1	mA	
Short-circuit output current	Ios	Vcc-5.25V	-30		-130	mA	
Supply current	Icc	Vcc-5.25V, Vi-4.5V (Output control)		_	24	40	mA
Input clamp voltage	Vik	$V_{cc}=4.75$ V, $I_{IN}=-18$ mA			-1.5	V	

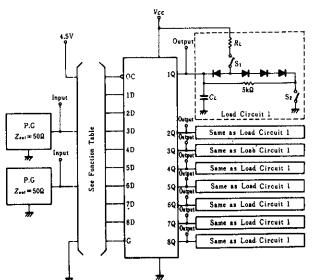
^{*} VCC=5V, Ta=25°C

ESWITCHING CHARACTERISTICS $(V_{cc}=5\text{V}, T_a=25^{\circ}\text{C})$

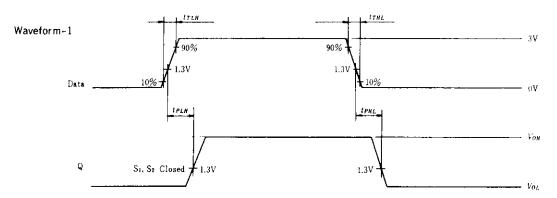
Item	Symbol	Input	Output	Test Conditions	min	typ	max	Unit
Propagation delay time	t _{PLH}	D Q			_	12	18	
	tpHL				12	18		
	t _{PLH}			$C_L = 45 \mathrm{pF}$		20	30	[
	t _{PHL}	G	Q	$R_L = 667\Omega$		18	30	ns
Output enable time tzH	t _{ZH}	ос			_	15	28] "15
	l ZL		Q		_	25	36]
	t _{HZ}	—— oc		$C_L = 5 pF$	_	12	20	
Output disable time	tLZ		Q	$R_L = 667\Omega$		15	25	

TESTING METHOD

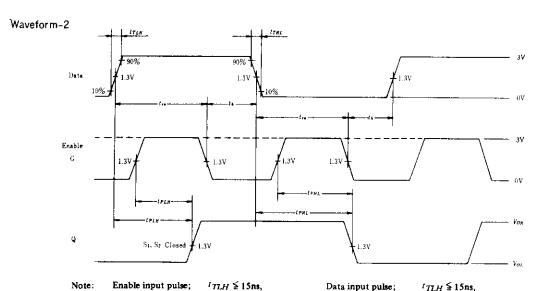
Test Circuit

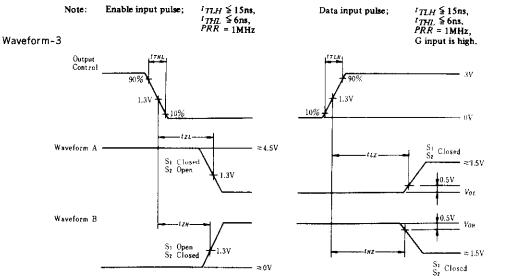


 C_L includes probe jig capacitance.
 All diodes are 1\$2074 (f). Notes:



Notes: Input pulse; $t_{TLH} \le 15$ ns, $t_{THL} \le 6$ ns, PRR = 1MHz, duty cycle 50%

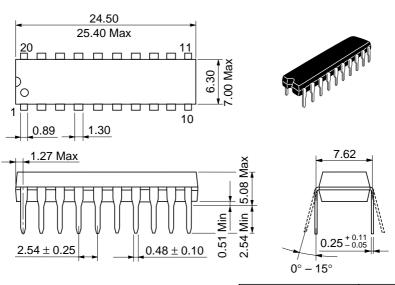




Notes:

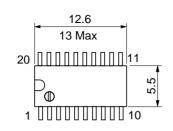
 Input pulse; t_{TLH} ≤ 15ns, t_{THL} ≤ 6ns, PRR = iMHz, duty cycle 50%
 Waveform A if for an output with internal conditions such that the output is low except when disabled by the output control. Waveform B is for an output with internal conditions such that the output is high except when disabled by the output control.

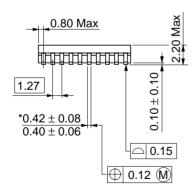
Unit: mm

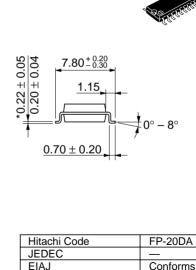


Hitachi Code	DP-20N
JEDEC	_
EIAJ	Conforms
Weight (reference value)	1.26 g

Unit: mm





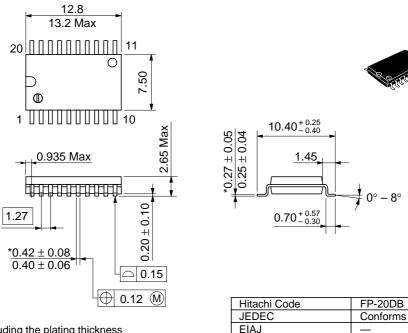


Weight (reference value)

0.31 g

*Dimension including the plating thickness
Base material dimension

Unit: mm



*Dimension including the plating thickness

Base material dimension

*EIAJ

Weight (reference value) 0.52 g

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